

## K. Memory (Design & Process Technology) 분과

Room B

창의관 (110)

일 시 : 2월 17일(금) 15:30-16:45

세션명 : [FB4-K] FLASH Memories and New Memory Technologies

좌 장 : 곽동화(삼성전자), 김영희(창원대학교)

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- FB4-K-1 15:30-15:45 **Layer Selection by Multi Level Operation (LSM) of String Select Line in 3D Stacked NAND Flash Memory**  
저자: Wandong Kim, Seung-Hyun Kim, Yoon Kim, Se-Hwan Park, Joo Yun Seo, Do-Bin Kim, and Byung-Gook Park  
소속: Inter-University Semiconductor Research Center and School of Electrical Engineering and Computer Science, Seoul National University
- FB4-K-2 15:45-16:00 **Erase Speed Enhancement by using SiGe Drain in 3D Stacked NAND Flash Memory**  
저자: Wandong Kim, Yoon Kim, Se-Hwan Park, Joo Yun Seo, Do-Bin Kim, Seung-Hyun Kim, and Byung-Gook Park  
소속: Inter-University Semiconductor Research Center and School of Electrical Engineering and Computer Science, Seoul National University
- FB4-K-3 16:00-16:15 **Dramatic Increase of Dielectric Constant of Al<sub>2</sub>O<sub>3</sub> by Very Light Doping of La and Thermal Treatment and Its Application to Flash Memory Device**  
저자: Jong Kyung Park<sup>1</sup>, Seok-Hee Lee<sup>1</sup>, Ki-Hong Lee<sup>2</sup>, Seung Ho Pyi<sup>2</sup>, and Byung Jin Cho<sup>1</sup>  
소속: <sup>1</sup>Department of Electrical Engineering, KAIST, <sup>2</sup>Hynix Semiconductor Inc.
- FB4-K-4 16:15-16:30 **Tri-states Memory using Ferroelectric-insulator-semiconductor Hetero-junctions for Fifty Percent Increased Data Storage**  
저자: Min Hyuk Park, Hyun Ju Lee, Gun Hwan Kim, Yu Jin Kim, Jeong Hwan Kim, Jong Ho Lee, and Cheol Seong Hwang  
소속: WCU Hybrid Materials Program, Department of Materials Science and Engineering, Seoul National University

FB4-K-5 16:30-16:45 Analysis of Fringe Field Effects in Nano-Electromechanical (NEM)  
Nonvolatile Memory Cells

저자: Boram Han and Woo Young Choi

소속: Department of Electronic Engineering, Sogang University